ShinEtsuMicroSi®

Dry-Etch Resistance Data of SEPR-I803D vs SEPR-I801

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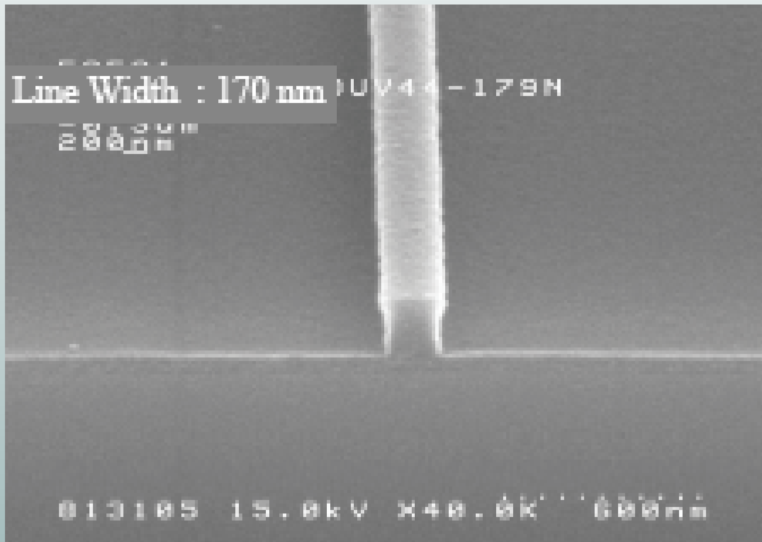
SEPR-I803D Dry-Etch Resistance Data

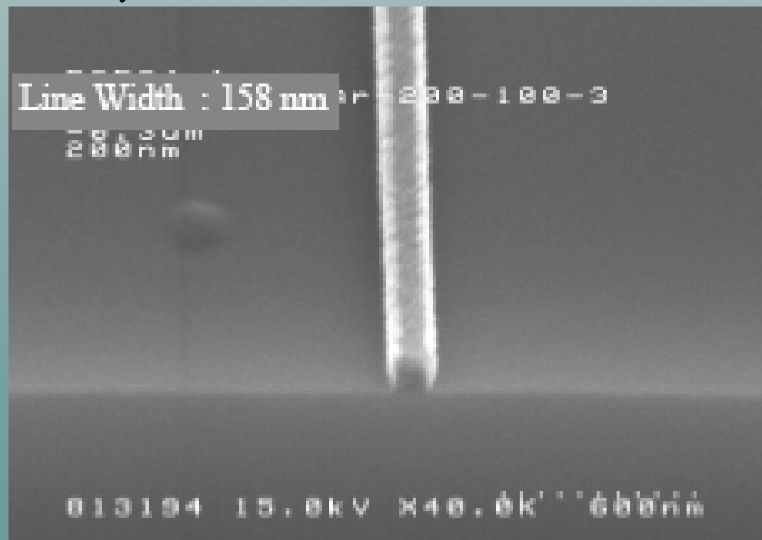
DUV-44 on Si Substrate
(FT:250nm , Mask : 200nm)

Film Thickness:250 nm Prebake: 110°Cx90 sec
Exp.: 40mJ/cm2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask: 200nm (Line Space =1/10) Focus: -0.3µm (Best Focus)
PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-179N [TMAH = 1.79%])

After Dev.



After Dry-Etch : Ar , 100 W X 3 min



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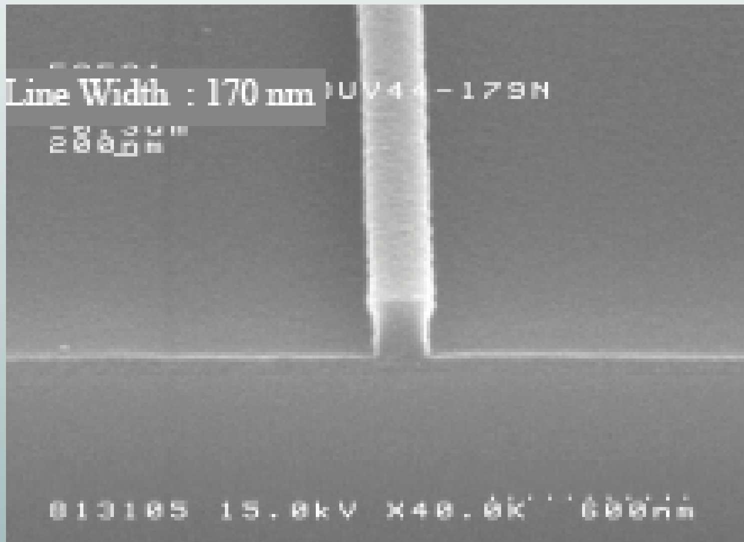
SEPR-I801 Dry-Etch Resistance Data

DUV-44 on Si Substrate (FT:250nm , Mask : 200nm)

Film Thickness:250 nm Prebake: 110°Cx90 sec
Exp.: 30mJ/cm2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask: 200nm (Line Space =1/10) Focus: -0.3μm (Best Focus)
PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-179N [TMAH = 1.79%])

After Dev.



After Dry-Etch : Ar , 100 W X 3 min